

## SHIPLEY 1813 POSITIVE TONE PHOTORESIST PROCESS

1. Substrate Dehydration: 10-minutes @ 110°C.
2. Adhesion Promoter Coating:  
Apply puddle HMDS on entire wafer and wait 5-10 seconds  
Spinning for 45 seconds @ 3500 RPM.
2. Photoresist coating.  
Cover about 50% of the substrate starting at the center  
Spread: 450 rpm 3 Second  
Spin: 45-sec @ 4000RPM for a resist for thickness of 1.3um  
Soft bake: vacuum hot plate at a temperature between at 1150°C for 60 seconds  
Exposure: 150 mJ (changes with transparent field of the mask)  
Develop: MF 319 for 45 second with agitation  
Rinse and Dry: Rinse with DI water for 30-60 seconds and dry with blowing nitrogen.

*For More information: talk to NCNC staff or refer to data sheet*